NTE
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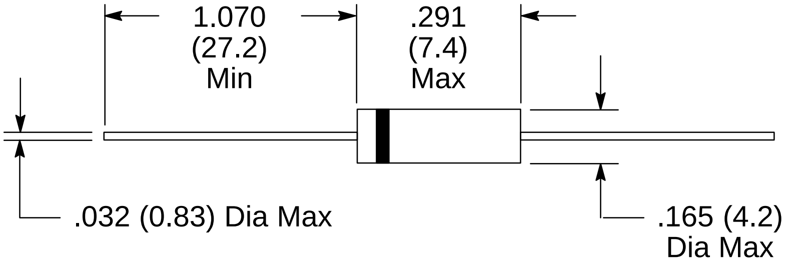
NTE570
Silicon Controlled Avalanche Diode

Absolute Maximum Ratings:

Peak Reverse Voltage, V_{RM}	130V
Allowable Avalanche Current (Square Wave Single Pulse 100µs), I_{ZSM}	1.0A
Operating Junction Temperature Range, T_J	–40° to +150°C
Storage temperature Range, T_{stg}	–40° to +150°C

Electrical Characteristics: (T_A = +25°C unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Avalanche Voltage	V_Z	I_Z = 1mA Instantaneous	135	–	180	V
Reverse Current	I_R	V_R = 130V	–	–	10	µA
Reverse Current (High Temperature)	$I_{R(H)}$	V_R = 130V, T_A = +100°C	–	–	50	µA
Temperature Dependency of V_Z	J	I_Z = 1mA	–	0.15	–	V/°C



Color Band Denotes Cathode